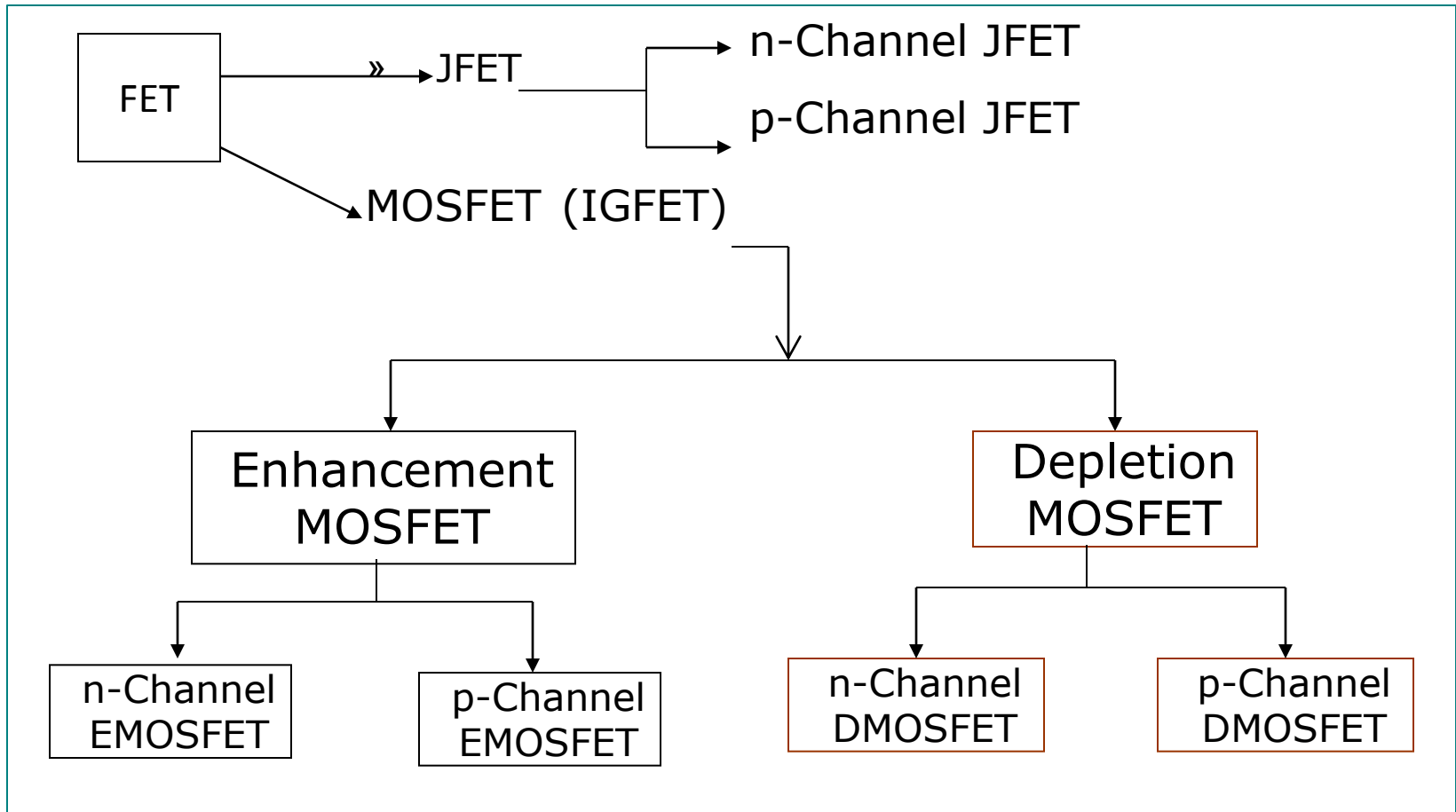


# FET ( Field Effect Transistor)

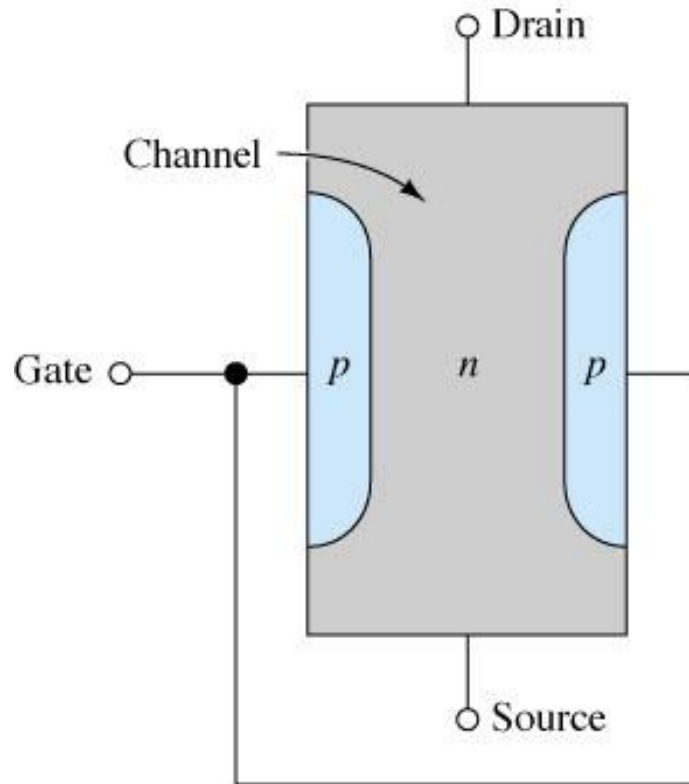
Few important advantages of FET over conventional Transistors

1. Unipolar device i. e. operation depends on only one type of charge carriers ( $h$  or  $e$ )
2. Voltage controlled Device (gate voltage controls drain current)
3. Very high input impedance ( $\approx 10^9$ - $10^{12} \Omega$ )
4. Source and drain are interchangeable in most Low-frequency applications
5. Low Voltage Low Current Operation is possible (Low-power consumption)
6. Less Noisy as Compared to BJT
7. No minority carrier storage (Turn off is faster)
8. Self limiting device
9. Very small in size, occupies very small space in ICs
10. Low voltage low current operation is possible in MOSFETS
11. Zero temperature drift of out put is possible

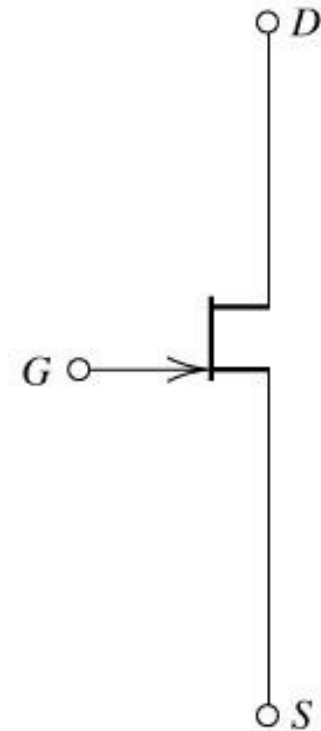
# Types of Field Effect Transistors (The Classification)



# The Junction Field Effect Transistor (JFET)



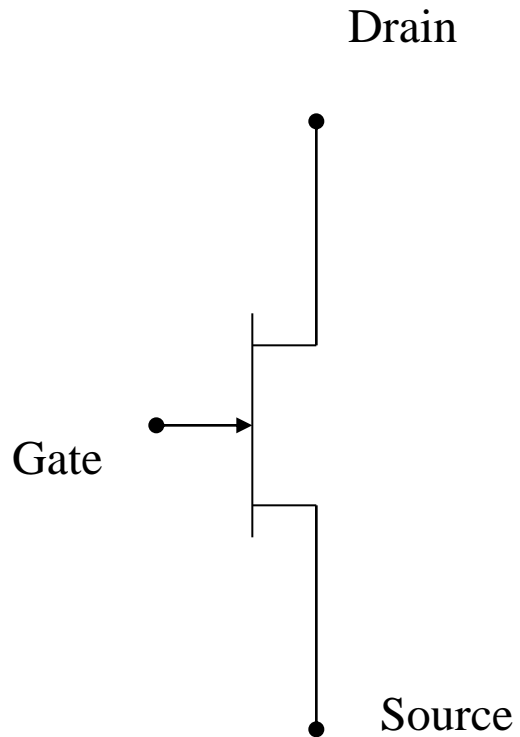
(a) Simplified physical structure



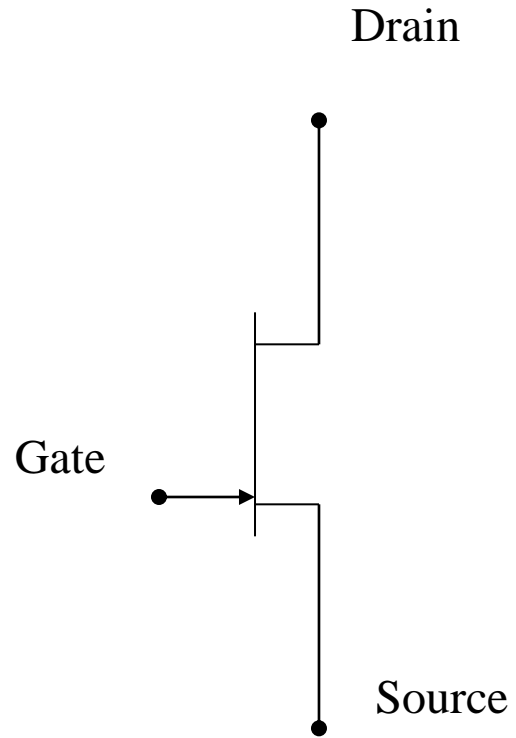
(b) Circuit symbol

**Figure:** *n*-Channel JFET.

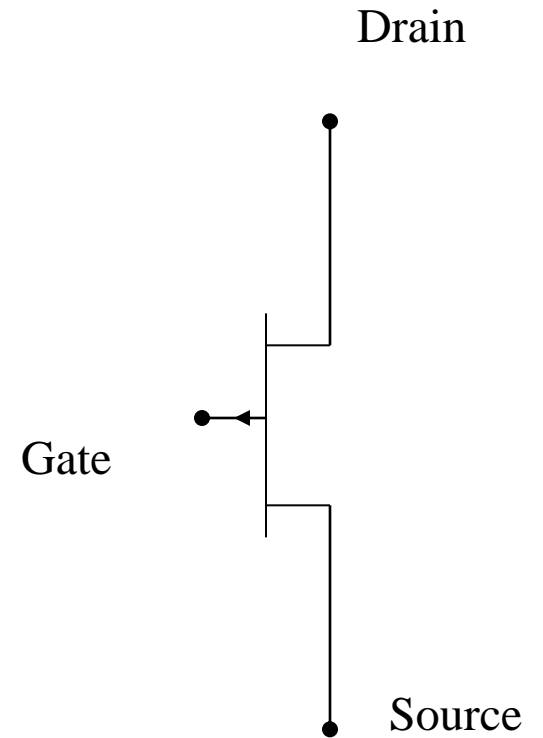
# SYMBOLS



n-channel JFET

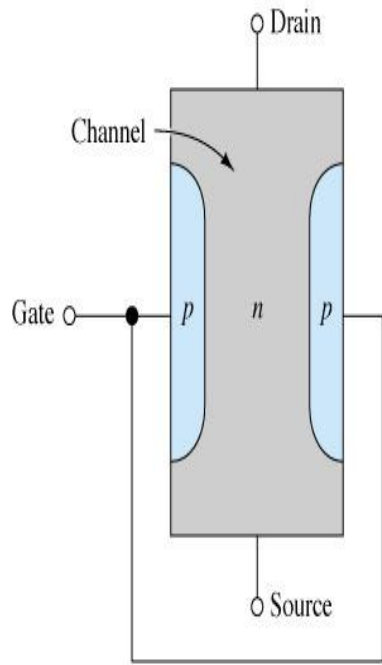


n-channel JFET  
Offset-gate symbol

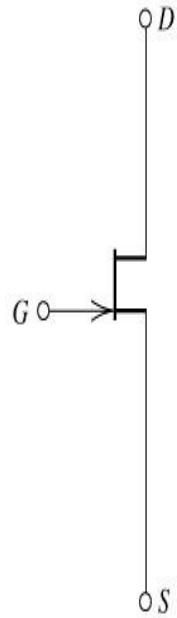


p-channel JFET

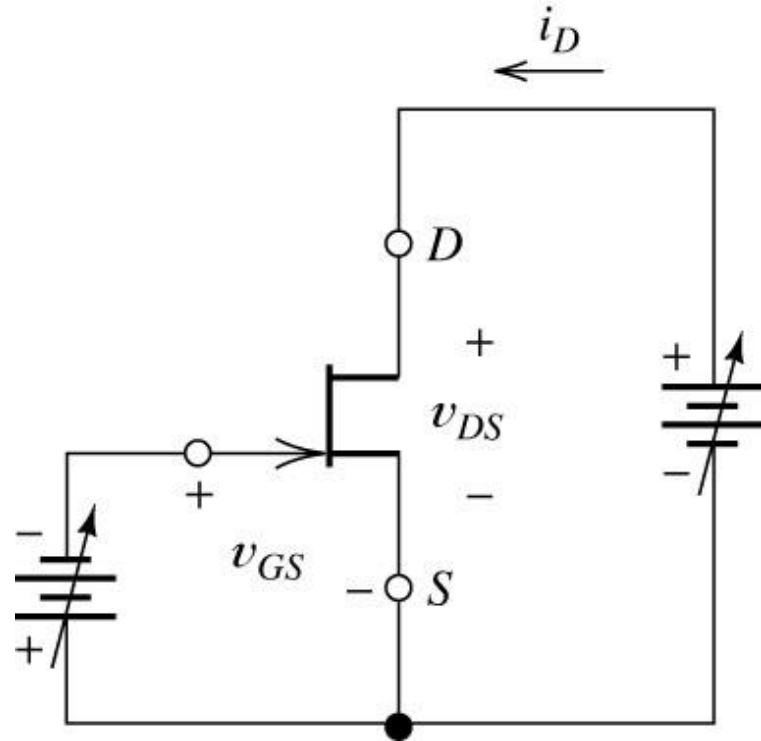
# Biassing the JFET



(a) Simplified physical structure

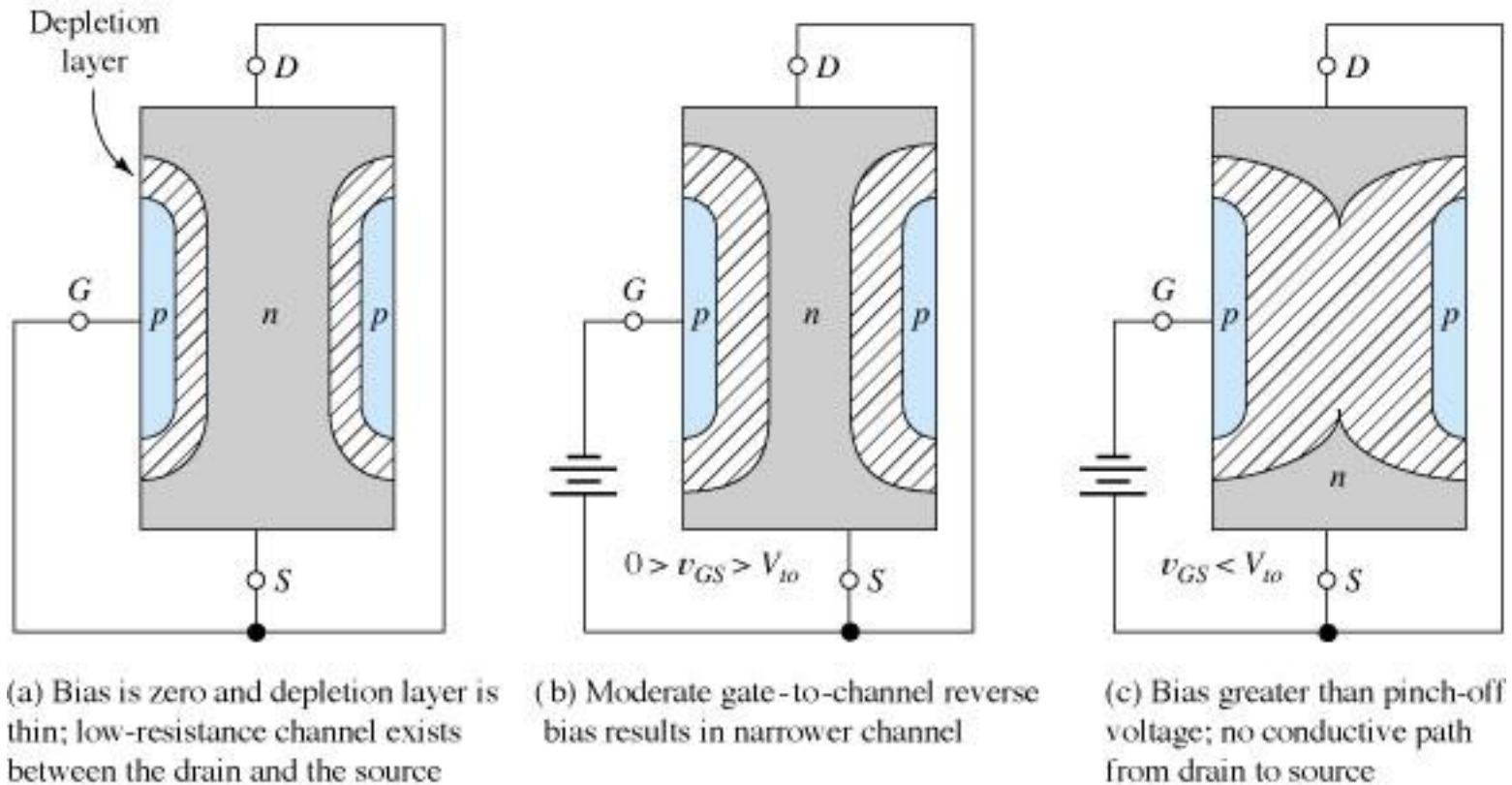


(b) Circuit symbol



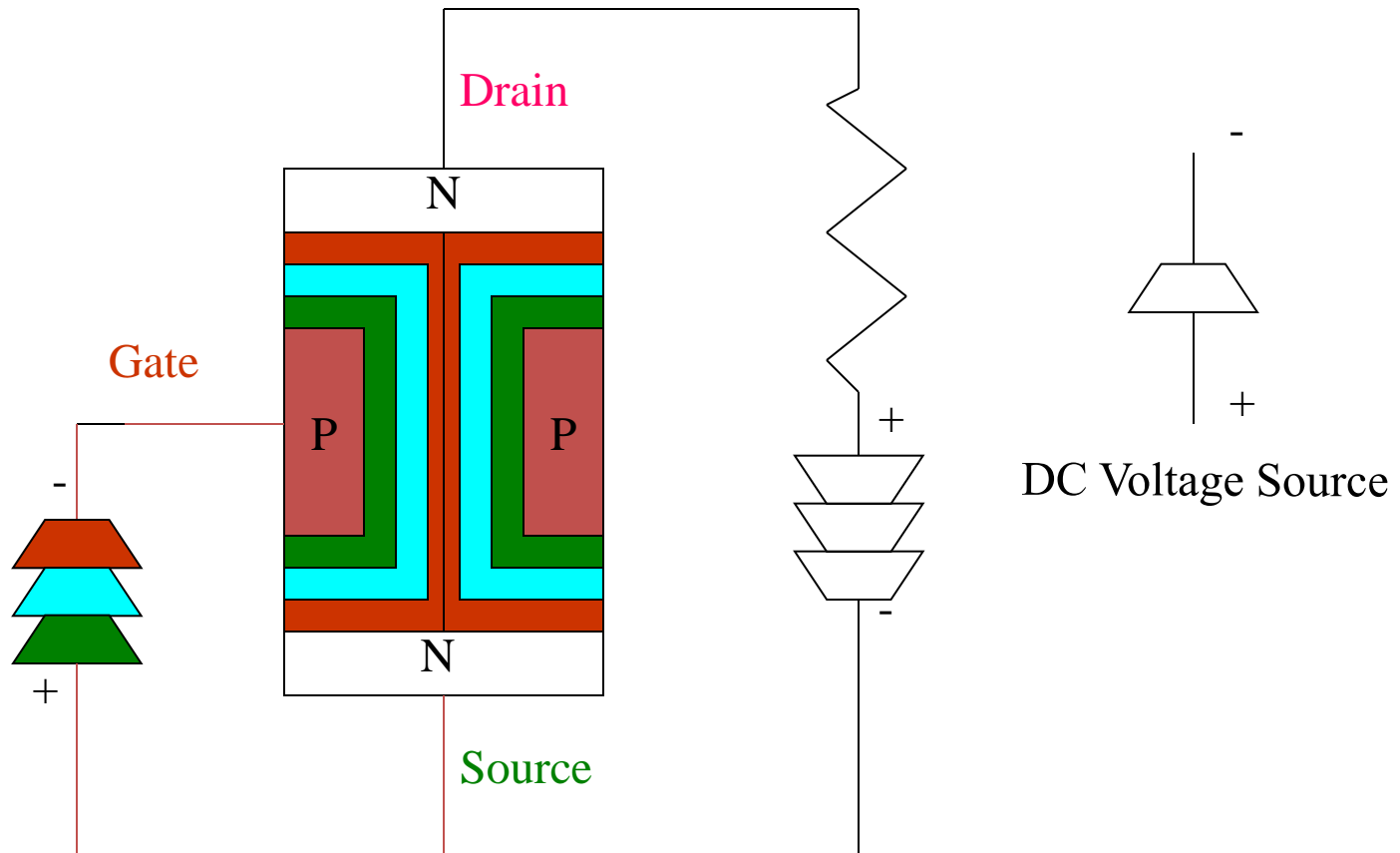
**Figure:** *n*-Channel JFET and Biasing Circuit.

# Operation of JFET at Various Gate Bias Potentials

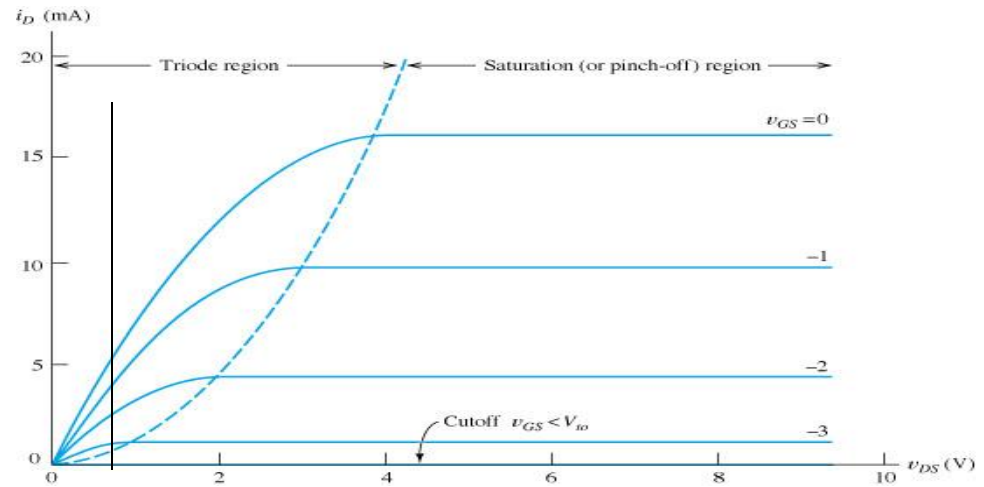
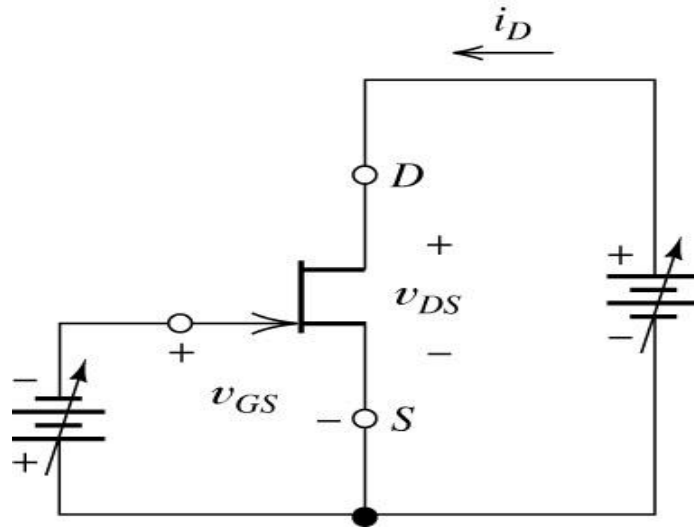


**Figure:** The nonconductive depletion region becomes broader with increased reverse bias.  
(Note: The two gate regions of each FET are connected to each other.)

# Operation of a JFET



# Output or Drain ( $V_D$ - $I_D$ ) Characteristics of n-JFET



**Figure:** Circuit for drain characteristics of the  $n$ -channel JFET and its Drain characteristics.

**Non-saturation (Ohmic) Region:**



$$V_{DS} < (V_{GS} - V_P)$$

The drain current is given by

$$I_{DS} = \frac{2I_{DSS}}{V_P^2} \left[ (V_{GS} - V_P)V_{DS} - \frac{V_{DS}^2}{2} \right]$$

**Saturation (or Pinchoff) Region:**



$$V_{DS} \geq (V_{GS} - V_P)$$

$$I_{DS} = \frac{I_{DSS}}{V_P^2} \left[ (V_{GS} - V_P)^2 \right] \quad \text{and} \quad I_{DS} = I_{DSS} \left( 1 - \frac{V_{GS}}{V_P} \right)^2$$

Where,  $I_{DSS}$  is the short circuit drain current,  $V_P$  is the pinch off voltage



# Simple Operation and Break down of n-Channel JFET

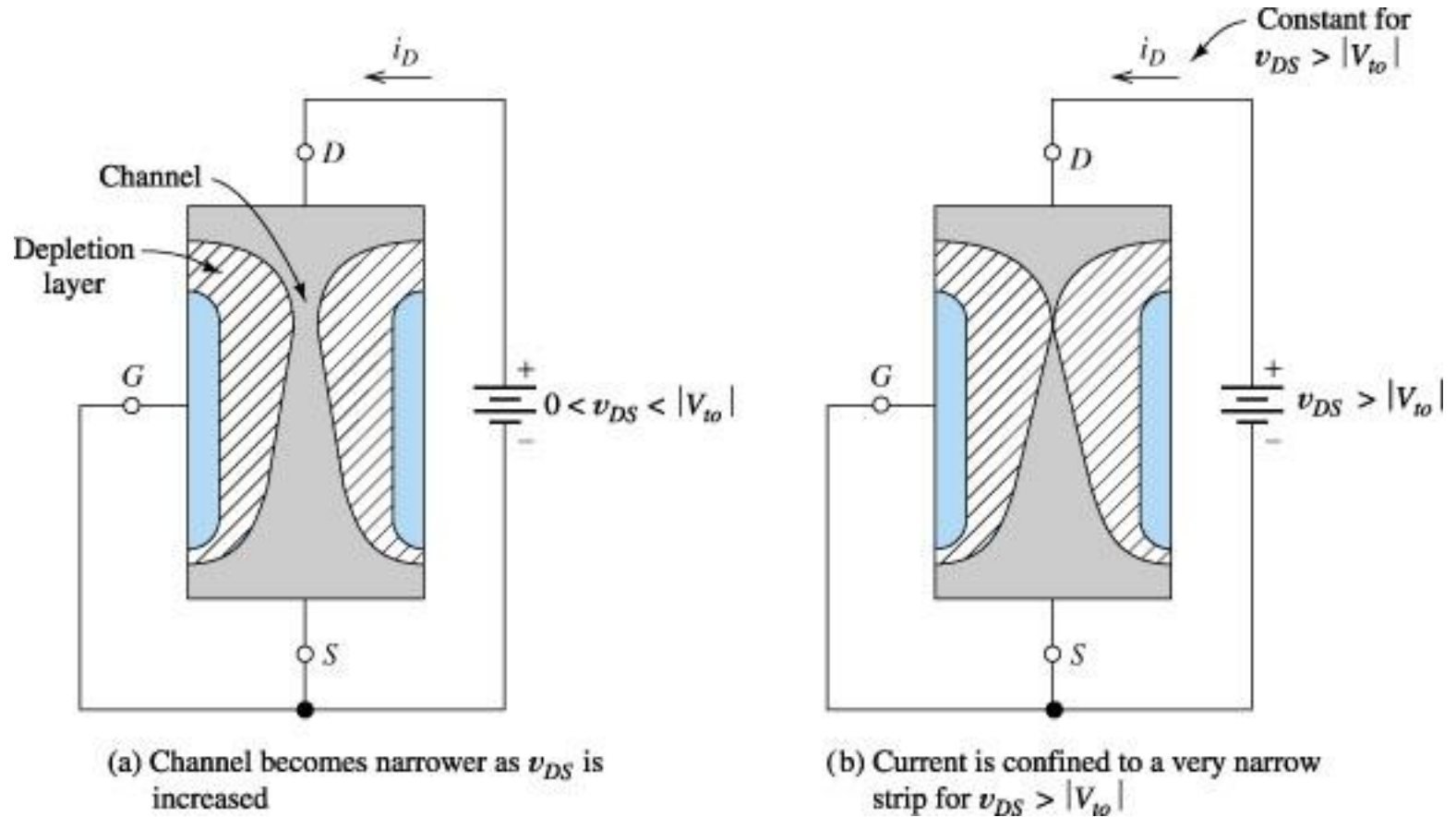


Figure: n-Channel FET for  $v_{GS} = 0$ .

# JFET Transfer Curve

This graph shows the value of  $I_D$  for a given value of  $V_{GS}$

